A method for manufacturing a hollow mems structure - DTU Orbit (31/03/2019)

A method for manufacturing a hollow mems structure
The present invention relates to a method for manufacturing an at least partly hollow MEMS structure. In a first step one or more through-going openings is/are provided in core material. The one or more through-going openings is/are then covered by an etch-stop layer. After this step, a bottom electrically conducting layer, one or more electrically conducting vias and a top electrically conducting layer are created. The bottom layer is connected to the vias and vias are connected to the top layer. The vias are formed by filling at least one of the one or more through-going openings. The method further comprises the step of creating bottom and top conductors in the respective bottom and top layers. Finally, excess core material is removed in order to create the at least partly hollow MEMS structure which may include a MEMS inductor.

General information
State: Published
Organisations: DTU Danchip, Department of Micro- and Nanotechnology, Silicon Microtechnology
Contributors: Han, A., Thanh, H. L., Birkelund, K., Jørgensen, A. M., Jensen, F.
Publication date: 29 Jun 2017

Publication information
IPC: H01F 17/00 A I
Patent number: WO2017108218
Date: 29/06/2017
Priority date: 23/12/2015
Priority number: EP20150202490
Original language: English
Electronic versions:
WO2017108218A1.pdf
Source: espacenet
Source-ID: WO2017108218
Research output: Research › Patent – Annual report year: 2017